

400V PNP HIGH VOLTAGE SWITCHING TRANSISTOR
Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

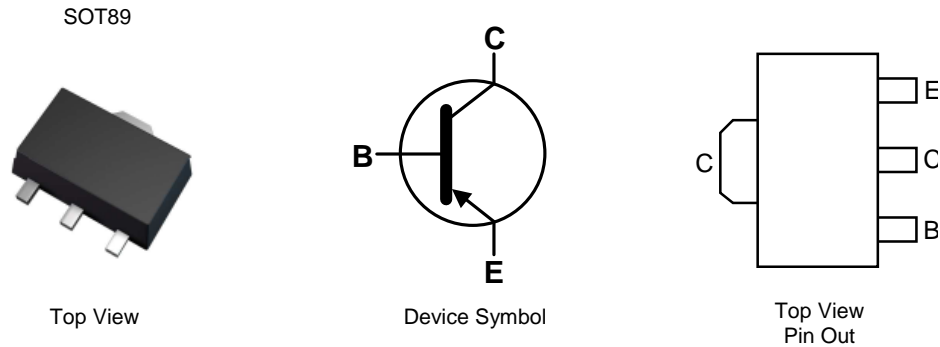
- $BV_{CEO} > -400V$
- $I_C = -0.5A$ Continuous Collector Current
- $I_{CM} = -1A$ Peak Pulse Current
- High Gain Holds up $h_{FE} \geq 140$ @ $I_C = -100mA$
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 0.05 grams (Approximate)

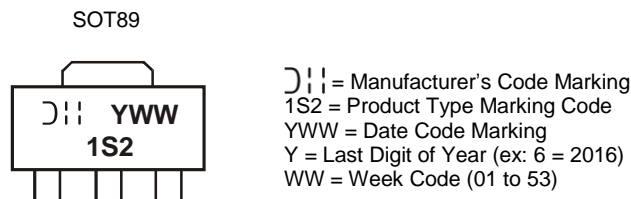
Applications

- High Voltage Switching


Ordering Information (Notes 4 and 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
2DA1971Q-7	Automotive	1S2	7	12	1,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-400	V
Collector-Emitter Voltage	V _{CEO}	-400	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-0.5	A
Peak Pulse Current	I _{CM}	-1	A
Base Current	I _B	-250	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

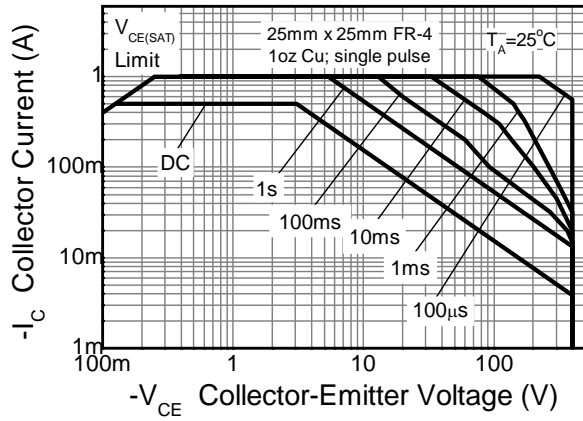
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	83	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{θJL}	10.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

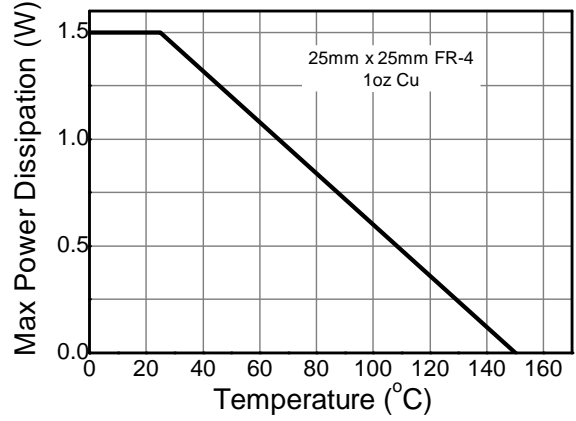
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

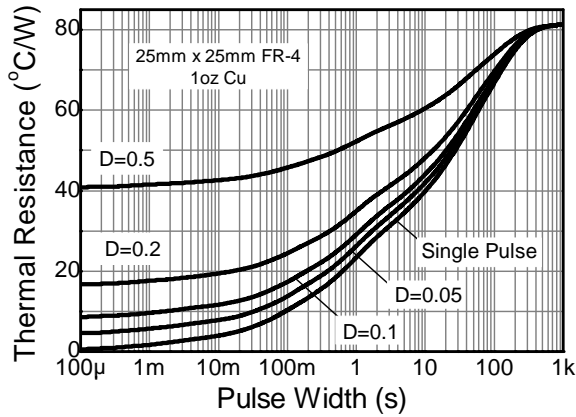
Thermal Characteristics and Derating information



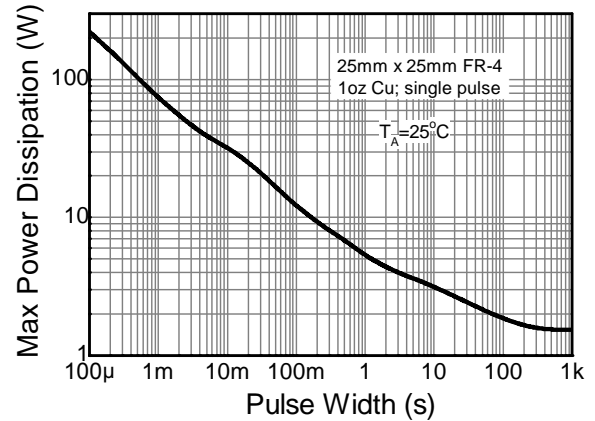
Safe Operating Area



Derating Curve



Transient Thermal Impedance



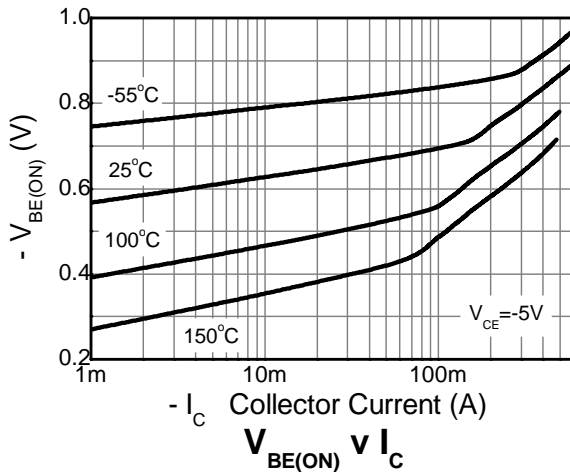
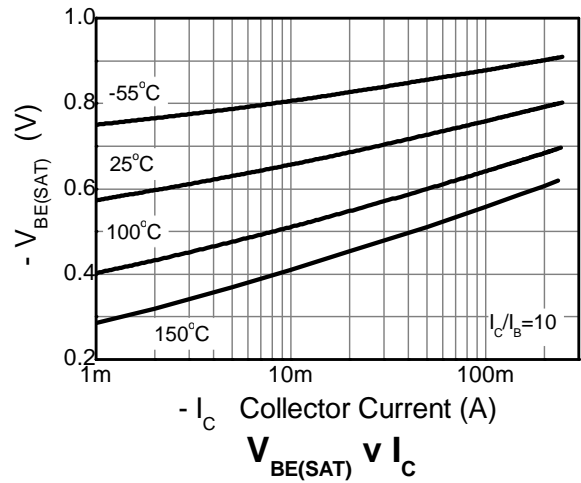
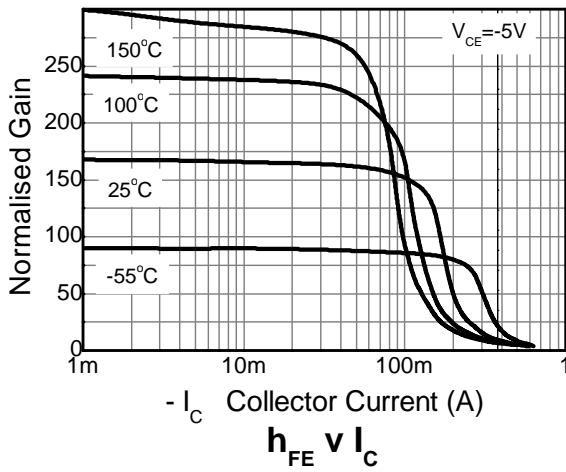
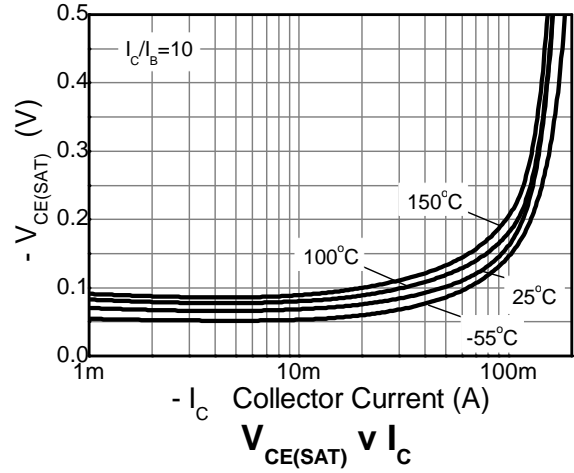
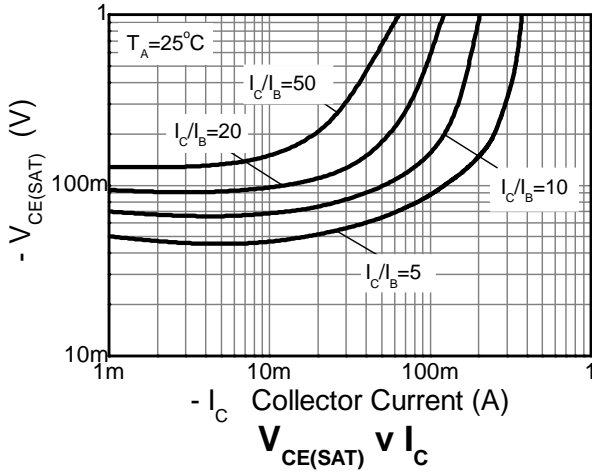
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-400	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-400	—	—	V	I _C = -1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	—	—	V	I _E = -100μA
Collector-Emitter Cut-off Current	I _{CES}	—	—	-100	nA	V _{CE} = -320V
Collector Cut-off Current	I _{CBO}	—	—	-100	nA	V _{CB} = -320V
Emitter Cut-off Current	I _{EBO}	—	—	-100	nA	V _{EB} = -6V
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	140 140	—	450 400	—	I _C = -20mA, V _{CE} = -5V I _C = -100mA, V _{CE} = -5V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}	—	—	-250 -400	mV	I _C = -100mA, I _B = -10mA I _C = -200mA, I _B = -40mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	—	-0.75	-0.9	V	I _C = -100mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	—	—	-0.8	V	I _C = -200mA, V _{CE} = -10V
Transition Frequency	f _T	—	75	—	MHz	I _C = -50mA, V _{CE} = -5V, f = 50MHz
Collector Output Capacitance	C _{OBO}	—	19	—	pF	V _{CB} = -10V, I _E = 0, f = 1MHz
Delay Time	t _(D)	—	89	—	ns	V _{CC} = -200V, I _C = -100mA, I _{B1} = -10mA, I _{B2} = 20mA
Rise Time	t _(R)	—	111	—	ns	
Storage Time	t _(S)	—	2165	—	ns	
Fall Time	t _(F)	—	185	—	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

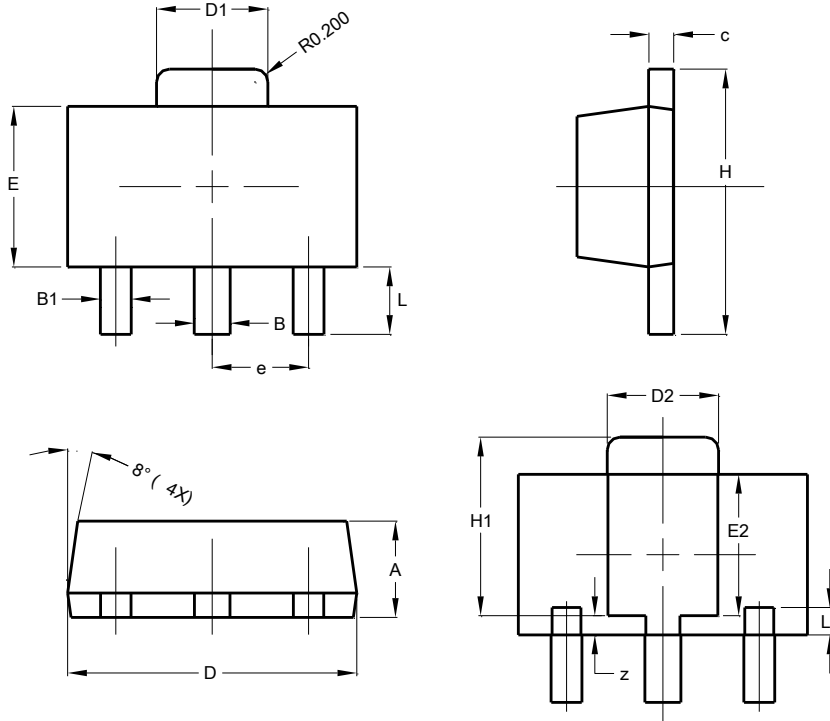
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89

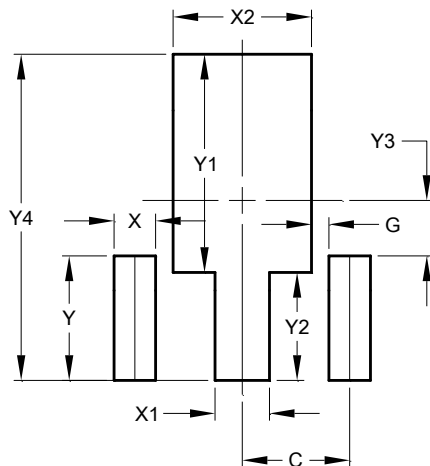


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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